L Number	Hits	Search Text	DB	Time stamp
1 Number	6271	(porous or porosity) same semiconductor	USPAT;	2004/03/24 08:25
1	02/1	(polous of polosity) same sameonaceor	US-PGPUB;	2001,03,21 00120
]		DERWENT	
2	3924	((porous or porosity) same semiconductor)	USPAT;	2004/03/24 08:31
-		and layer\$3 same semiconductor	US-PGPUB;	
			DERWENT	
3	2509	(((porous or porosity) same semiconductor)	USPAT;	2004/03/24 08:26
		and layer\$3 same semiconductor) and	US-PGPUB;	
		(porous or porosity) near8 layer\$4	DERWENT	
4	810	((((porous or porosity) same	USPAT;	2004/03/24 08:27
		semiconductor) and layer\$3 same	US-PGPUB;	
	1	semiconductor) and (porous or porosity)	DERWENT	·
		near8 layer\$4) and (upper or lower or		
_		central or intermediate) near3 layer\$4	TIGDAM.	0004/03/04 00 07
5	6	(((((porous or porosity) same	USPAT;	2004/03/24 08:27
		semiconductor) and layer\$3 same	US-PGPUB;	
		semiconductor) and (porous or porosity)	DERWENT	
		near8 layer\$4) and (upper or lower or central or intermediate) near3 layer\$4)		
		and 435/6.ccls.		
6	0	(((((porous or porosity) same	USPAT;	2004/03/24 08:27
	1	semiconductor) and layer\$3 same	US-PGPUB;	
		semiconductor) and (porous or porosity)	DERWENT	}
		near8 layer\$4) and (upper or lower or		
		central or intermediate) near3 layer\$4)		
		and 483.1.ccls.		
7	0	(((((porous or porosity) same	USPAT;	2004/03/24 08:27
		semiconductor) and layer\$3 same	US-PGPUB;	
		semiconductor) and (porous or porosity)	DERWENT	i
		near8 layer\$4) and (upper or lower or	*	
		central or intermediate) near3 layer\$4)		
		and 435/423.1.ccls.		
8	0	(((((porous or porosity) same	USPAT;	2004/03/24 08:27
		semiconductor) and layer\$3 same	US-PGPUB;	÷
		semiconductor) and (porous or porosity)	DERWENT	
ļ		near8 layer\$4) and (upper or lower or central or intermediate) near3 layer\$4)		
		and 422/68.1.ccls.		
9	9	(((((porous or porosity) same	USPAT;	2004/03/24 08:28
		semiconductor) and layer\$3 same	US-PGPUB;	
		semiconductor) and (porous or porosity)	DERWENT	
		near8 layer\$4) and (upper or lower or		}
		central or intermediate) near3 layer\$4)		
		and (biosensor or biochip)		1
10	9	((((((porous or porosity) same	USPAT;	2004/03/24 08:30
		semiconductor) and layer\$3 same	US-PGPUB;	
	ļ	semiconductor) and (porous or porosity)	DERWENT	
		near8 layer\$4) and (upper or lower or		
		central or intermediate) near3 layer\$4)		
		and (biosensor or biochip)) or		
	ļ	((((((porous or porosity) same		
		semiconductor) and layer\$3 same semiconductor) and (porous or porosity)		· .
		near8 layer\$4) and (upper or lower or		
		central or intermediate) near3 layer\$4)		
		and 435/6.ccls.)		
12	5		USPAT;	2004/03/24 08:31
		semiconductor) and layer\$3 same	US-PGPUB;	
		semiconductor) and (porous or porosity)	DERWENT	
		near8 layer\$4) and bragg same		
		semiconductor		
11	35		USPAT;	2004/03/24 08:32
		semiconductor) and layer\$3 same	US-PGPUB;	
		semiconductor) and (porous or porosity)	DERWENT	
		near8 layer\$4) and alternat\$4 near2		
13		(porous or porosity)	HCDAG	2004/02/04 00:41
14	17	6194239.URPN. 6107213.URPN.	USPAT	2004/03/24 08:41
T.4	1	OTO/STO.UKEN.	USPAT	2004/03/24 09:18